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(54) Title: METHOD FOR REDUCING MICROLOADING IN ETCHING HIGH ASPECT RATIO STRUCTURES

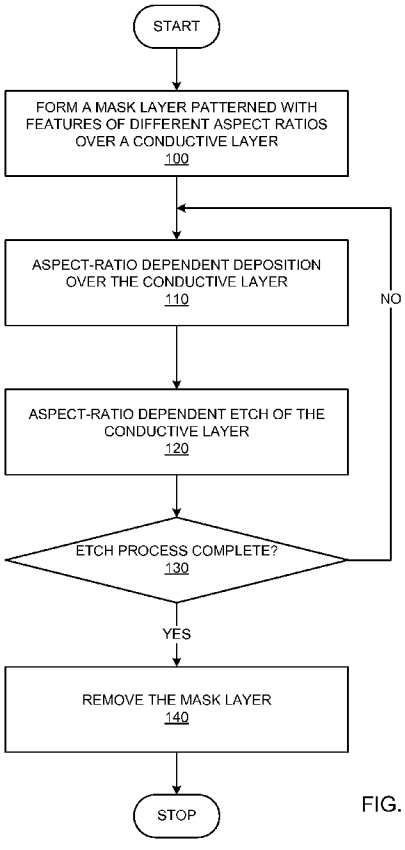


FIG. 1

(57) Abstract: A method for etching features of different aspect ratios in a conductive layer is provided. The method comprises: depositing over the conductive layer with an aspect ratio dependent deposition; etching features into the conductive layer with an aspect ratio dependent etching of the conductive layer; and repeating the depositing and the etching at least once.

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